

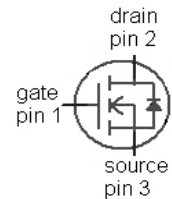
OptiMOS™ 3 Power-Transistor
Features

- Ideal for high frequency switching
- Optimized technology for DC/DC converters
- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- N-channel, normal level
- 100% avalanche tested
- Pb-free plating; RoHS compliant
- Qualified according to JEDEC¹⁾ for target applications
- Halogen-free according to IEC61249-2-21


Product Summary

V_{DS}	80	V
$R_{DS(on),max}$ (SMD)	13.6	m Ω
I_D	45	A

Type	IPP139N08N3 G	IPI139N08N3 G	IPB136N08N3 G
Package	PG-TO-220-3	PG-TO-262-3	PG-TO-263-3
Marking	139N08N	139N08N	136N08N


Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	$T_C=25\text{ °C}$	45	A
		$T_C=100\text{ °C}$	39	
Pulsed drain current ²⁾	$I_{D,pulse}$	$T_C=25\text{ °C}$	180	
Avalanche energy, single pulse ³⁾	E_{AS}	$I_D=45\text{ A}$, $R_{GS}=25\ \Omega$	50	mJ
Gate source voltage	V_{GS}		± 20	V
Power dissipation	P_{tot}	$T_C=25\text{ °C}$	79	W
Operating and storage temperature	T_j , T_{stg}		-55 ... 175	°C
IEC climatic category; DIN IEC 68-1			55/175/56	

¹⁾J-STD20 and JESD22

²⁾ See figure 3 for more detailed information

³⁾ See figure 13 for more detailed information

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}		-	-	1.9	K/W
Thermal resistance, junction - ambient	R_{thJA}	minimal footprint	-	-	62	
		6 cm ² cooling area ⁴⁾	-	-	40	

Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified
Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}, I_D=1\text{ mA}$	80	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=33\text{ }\mu\text{A}$	2	2.8	3.5	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=80\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ °C}$	-	0.1	1	μA
		$V_{DS}=80\text{ V}, V_{GS}=0\text{ V}, T_j=125\text{ °C}$	-	10	100	
Gate-source leakage current	I_{GSS}	$V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$	-	1	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}, I_D=45\text{ A}$	-	11.8	13.9	$\text{m}\Omega$
		$V_{GS}=6\text{ V}, I_D=22.5\text{ A}$	-	16.0	26	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}, I_D=45\text{ A},$ (SMD)	-	11.5	13.6	
		$V_{GS}=6\text{ V}, I_D=22.5\text{ A},$ (SMD)	-	16.0	26.0	
Gate resistance	R_G		-	2	-	Ω
Transconductance	g_{fs}	$ V_{DS} >2 I_D R_{DS(on)max},$ $I_D=45\text{ A}$	24	48	-	S

⁴⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics

Input capacitance	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=40\text{ V},$ $f=1\text{ MHz}$	-	1300	1730	pF
Output capacitance	C_{oss}		-	353	469	
Reverse transfer capacitance	C_{rss}		-	15	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=40\text{ V}, V_{GS}=10\text{ V},$ $I_D=45\text{ A}, R_G=1.6\ \Omega$	-	12	-	ns
Rise time	t_r		-	35	-	
Turn-off delay time	$t_{d(off)}$		-	18	-	
Fall time	t_f		-	5	-	

Gate Charge Characteristics⁵⁾

Gate to source charge	Q_{gs}	$V_{DD}=40\text{ V}, I_D=45\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	7	-	nC
Gate to drain charge	Q_{gd}		-	4	-	
Switching charge	Q_{sw}		-	8	-	
Gate charge total	Q_g		-	19	25	
Gate plateau voltage	$V_{plateau}$		-	5.5	-	V
Output charge	Q_{oss}	$V_{DD}=40\text{ V}, V_{GS}=0\text{ V}$	-	25	34	nC

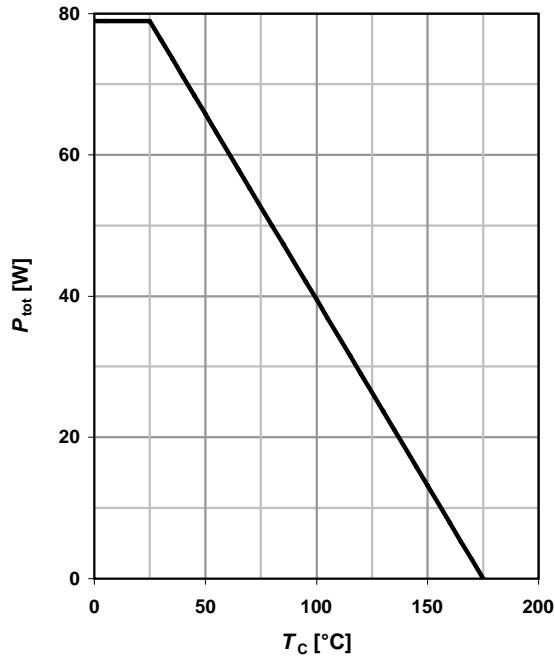
Reverse Diode

Diode continuous forward current	I_S	$T_C=25\text{ }^\circ\text{C}$	-	-	45	A
Diode pulse current	$I_{S,pulse}$		-	-	180	
Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=45\text{ A},$ $T_j=25\text{ }^\circ\text{C}$	-	1.0	1.2	V
Reverse recovery time	t_{rr}	$V_R=40\text{ V}, I_F=I_S,$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	50	-	ns
Reverse recovery charge	Q_{rr}		-	74	-	nC

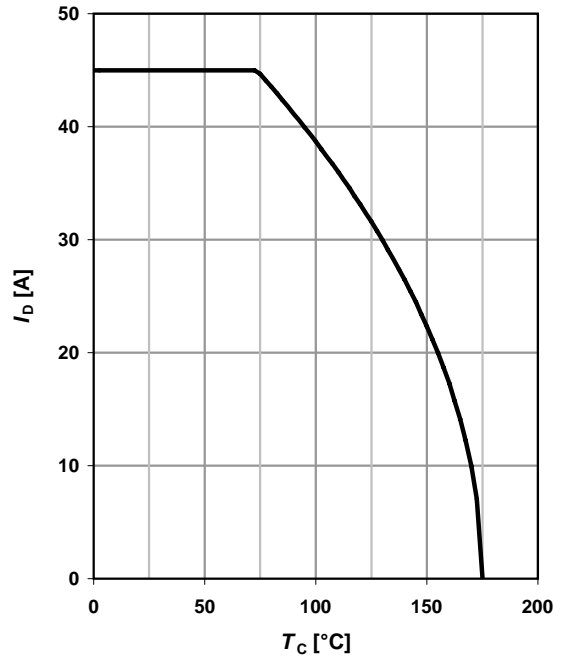
⁵⁾ See figure 16 for gate charge parameter definition

1 Power dissipation

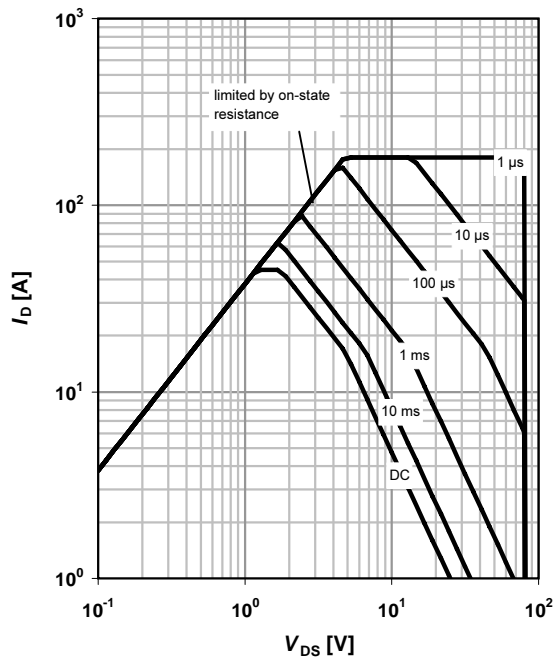
$$P_{\text{tot}} = f(T_C)$$


2 Drain current

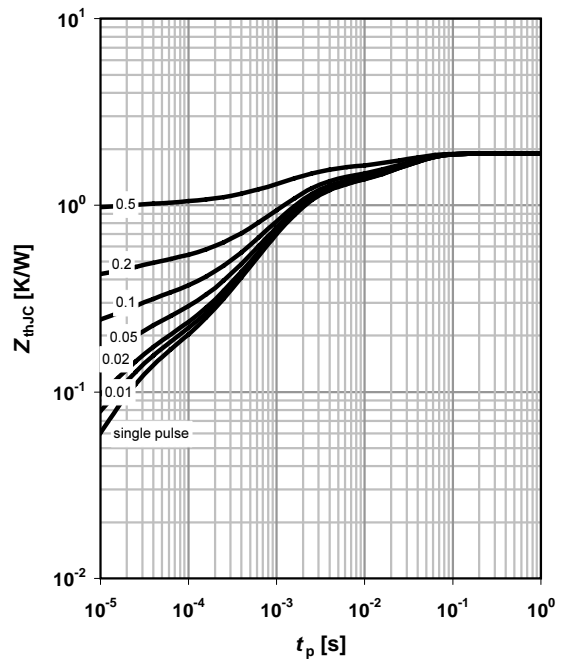
$$I_D = f(T_C); V_{GS} \geq 10 \text{ V}$$


3 Safe operating area

$$I_D = f(V_{DS}); T_C = 25^\circ\text{C}; D = 0$$

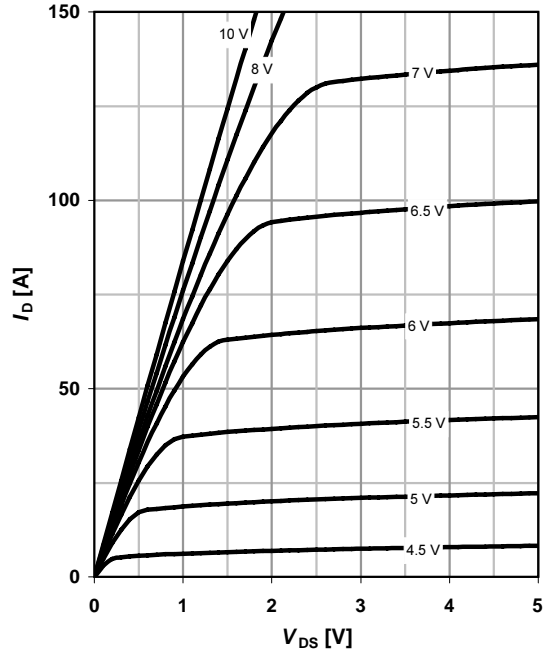
 parameter: t_p

4 Max. transient thermal impedance

$$Z_{\text{thJC}} = f(t_p)$$

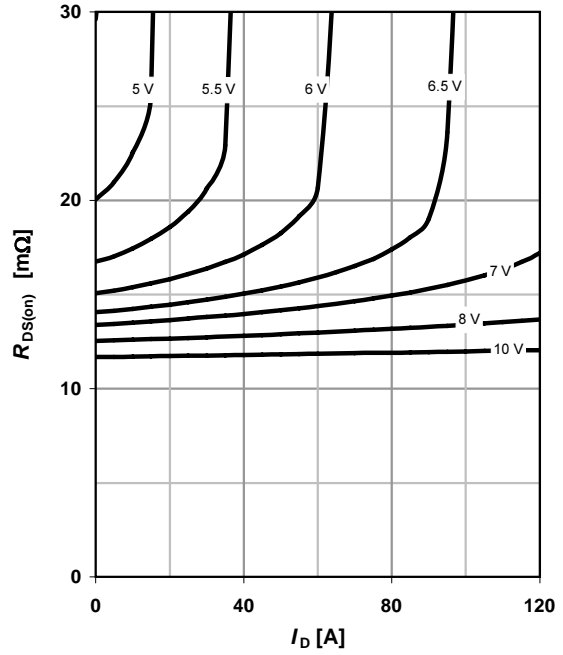
 parameter: $D = t_p/T$


5 Typ. output characteristics

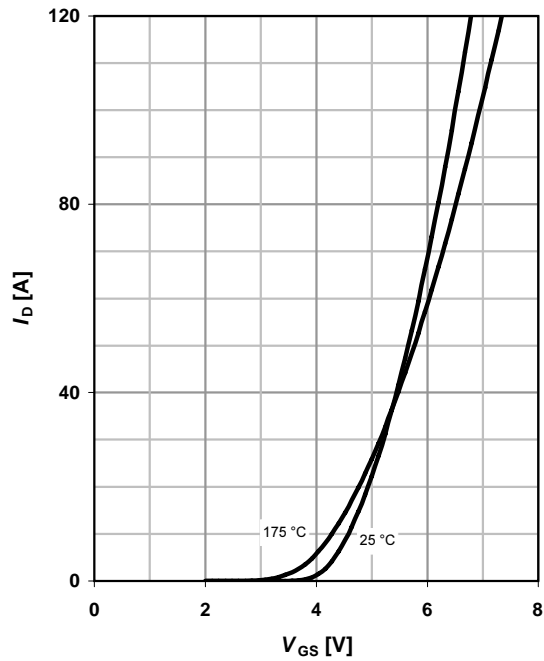
$$I_D = f(V_{DS}); T_j = 25\text{ °C}$$

 parameter: V_{GS}

6 Typ. drain-source on resistance

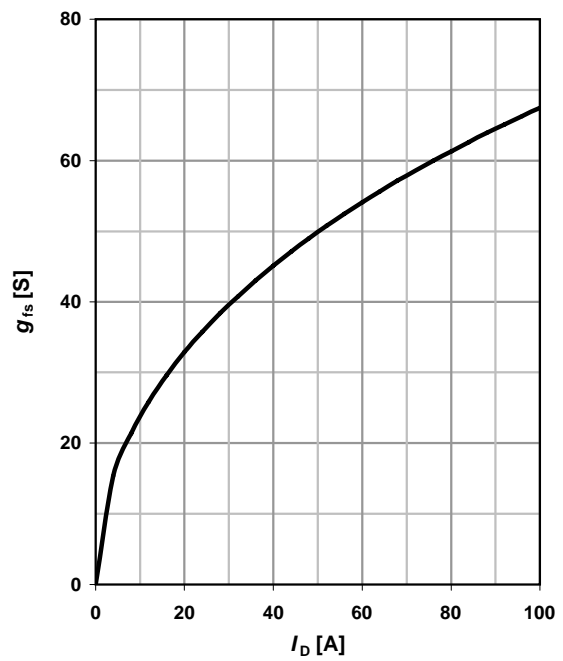
$$R_{DS(on)} = f(I_D); T_j = 25\text{ °C}$$

 parameter: V_{GS}

7 Typ. transfer characteristics

$$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$$

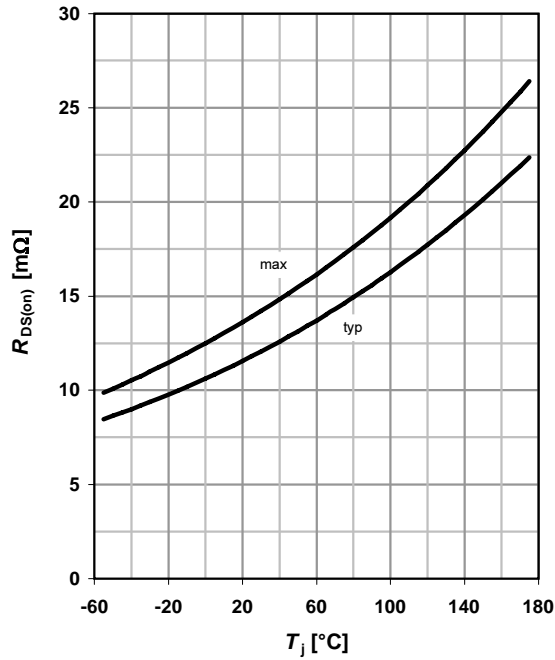
 parameter: T_j

8 Typ. forward transconductance

$$g_{fs} = f(I_D); T_j = 25\text{ °C}$$

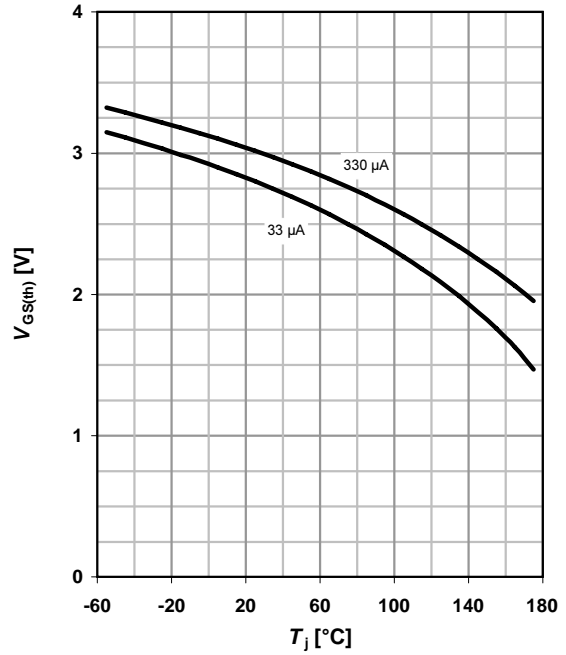


9 Drain-source on-state resistance

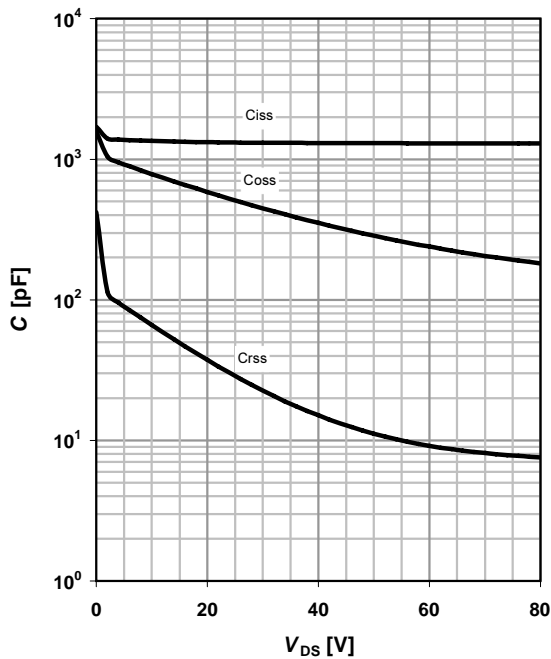
$$R_{DS(on)} = f(T_j); I_D = 45 \text{ A}; V_{GS} = 10 \text{ V}$$


10 Typ. gate threshold voltage

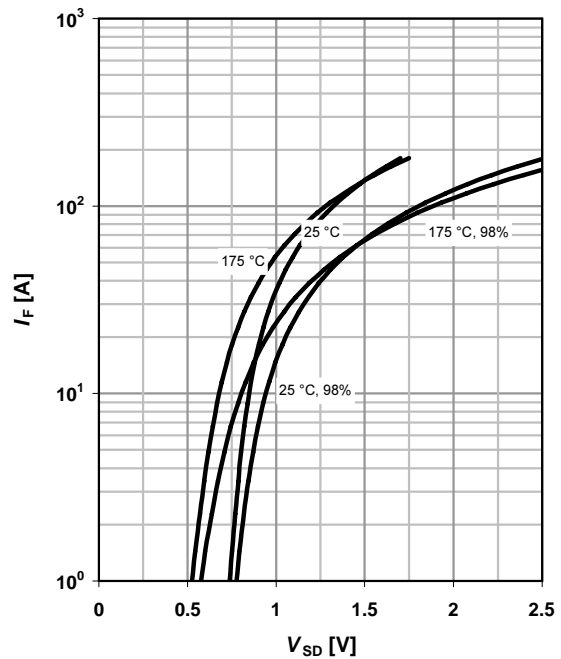
$$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$$

 parameter: I_D

11 Typ. capacitances

$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$


12 Forward characteristics of reverse diode

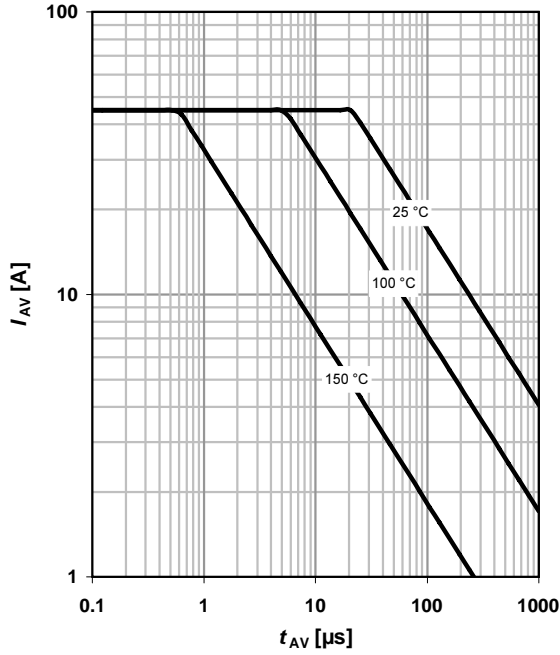
$$I_F = f(V_{SD})$$

 parameter: T_j


13 Avalanche characteristics

$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$

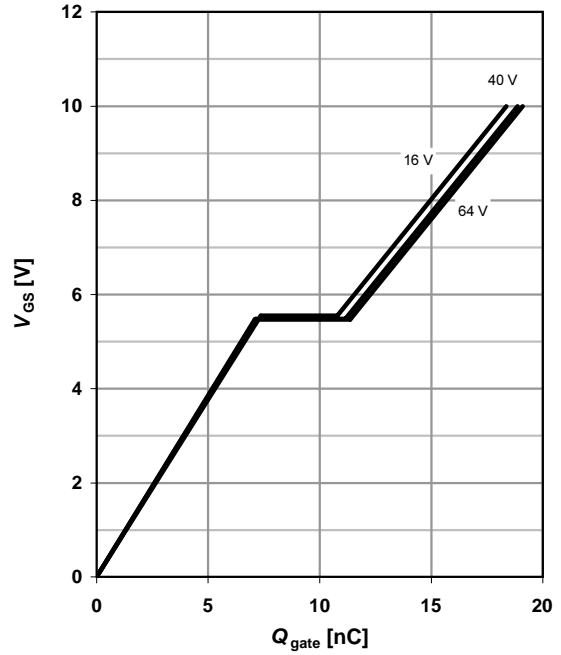
parameter: $T_{j(start)}$



14 Typ. gate charge

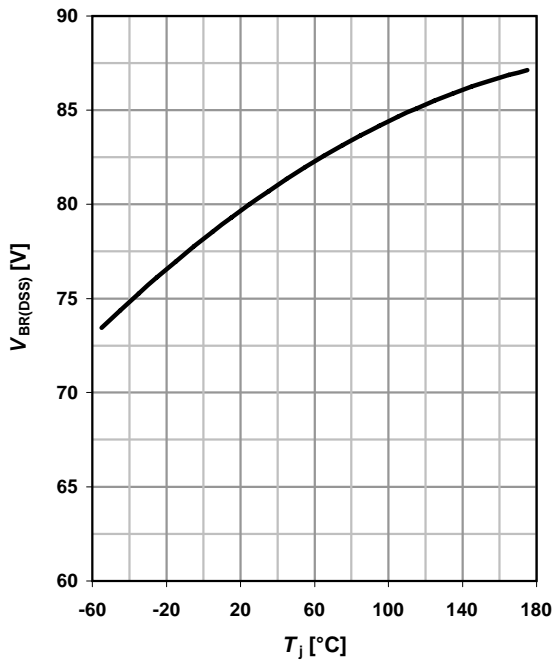
$V_{GS}=f(Q_{gate}); I_D=45 \text{ A pulsed}$

parameter: V_{DD}

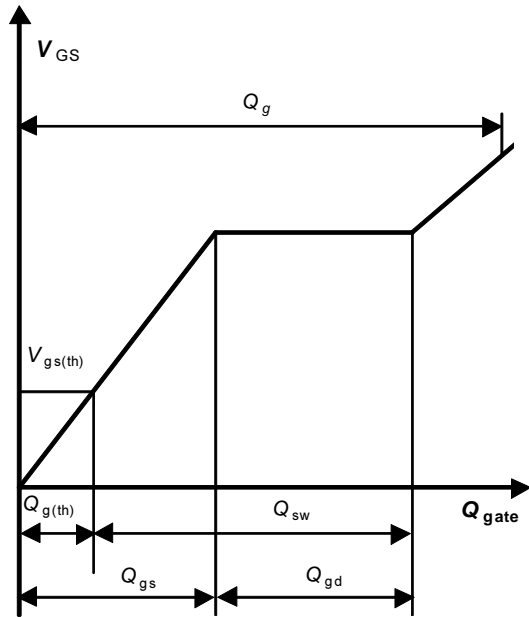


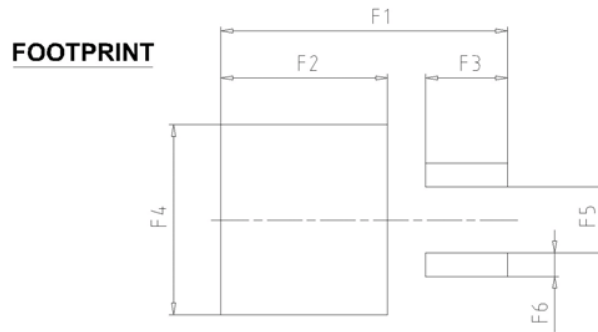
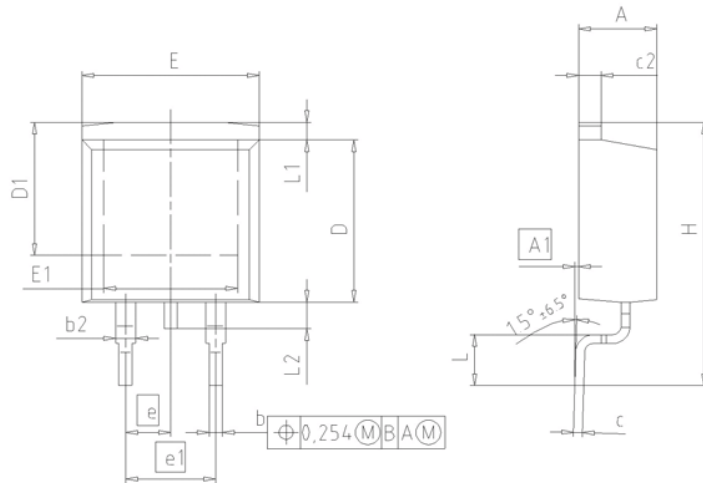
15 Drain-source breakdown voltage

$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$



16 Gate charge waveforms

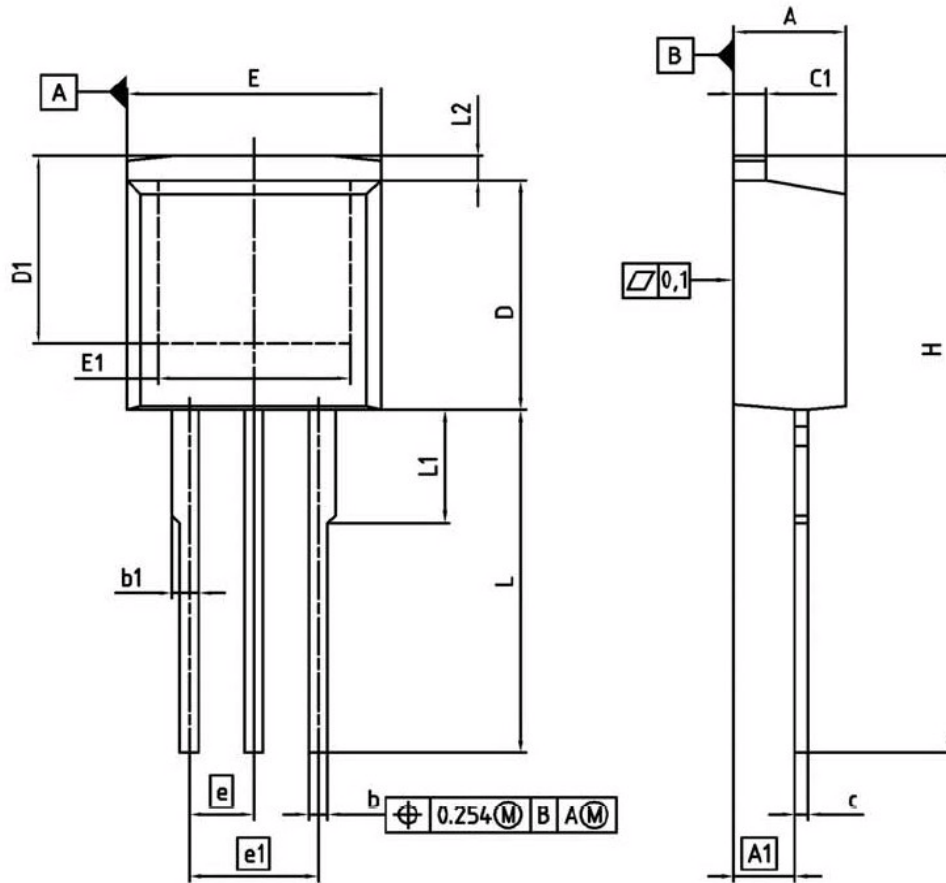


PG-TO-263-3 (D²-Pak)


DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	0.00	0.25	0.000	0.010
b	0.65	0.85	0.026	0.033
b2	0.95	1.15	0.037	0.045
c	0.33	0.65	0.013	0.026
c2	1.17	1.40	0.046	0.055
D	8.51	9.45	0.335	0.372
D1	7.10	7.90	0.280	0.311
E	9.80	10.31	0.386	0.406
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	2		2	
H	14.61	15.88	0.575	0.625
L	2.29	3.00	0.090	0.118
L1	0.70	1.60	0.028	0.063
L2	1.00	1.78	0.039	0.070
F1	16.05	16.25	0.632	0.640
F2	9.30	9.50	0.366	0.374
F3	4.50	4.70	0.177	0.185
F4	10.70	10.90	0.421	0.429
F5	3.65	3.85	0.144	0.152
F6	1.25	1.45	0.049	0.057

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SCALE 0 5 5 7.5mm
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REVISION 01

PG-TO-262-3 (I²-Pak)



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.300	4.572	0.169	0.180
A1	2.150	2.718	0.085	0.107
b	0.650	0.664	0.026	0.034
b1	0.635	1.400	0.025	0.055
c	0.330	0.600	0.013	0.024
c1	1.170	1.400	0.046	0.055
D	8.509	9.450	0.335	0.372
D1	6.900	-	0.272	-
E	9.700	10.363	0.382	0.408
E1	6.500	8.600	0.256	0.339
e	2.540		0.100	
e1	5.080		0.200	
N	3		3	
L	13.000	14.000	0.512	0.551
L1	-	4.800	-	0.189
L2	-	1.727	-	0.068

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